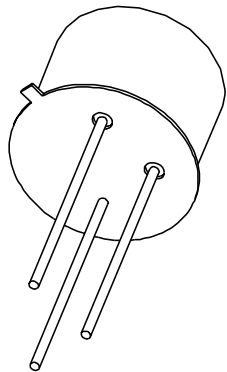


DATA SHEET



2N3019 NPN medium power transistor

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Jun 19

NPN medium power transistor

2N3019

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

APPLICATIONS

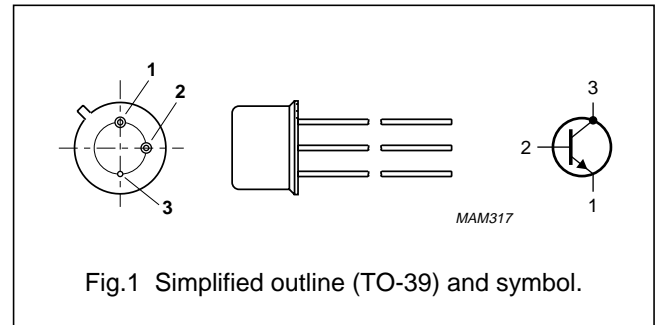
- Amplifier and switching circuits.

DESCRIPTION

NPN medium power transistor in a TO-39 metal package.

PINNING

| PIN | DESCRIPTION |
|-----|------------------------------|
| 1 | emitter |
| 2 | base |
| 3 | collector, connected to case |



QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|---------------------------|--|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | – | 140 | V |
| V_{CEO} | collector-emitter voltage | open base | – | 80 | V |
| I_C | collector current (DC) | | – | 1 | A |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ }^\circ\text{C}$ | – | 800 | mW |
| | | $T_{case} \leq 25\text{ }^\circ\text{C}$ | – | 5 | W |
| h_{FE} | DC current gain | $I_C = 150\text{ mA}; V_{CE} = 10\text{ V}$ | 100 | 300 | |
| f_T | transition frequency | $I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$ | 100 | – | MHz |

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|---------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | – | 140 | V |
| V _{CEO} | collector-emitter voltage | open base | – | 80 | V |
| V _{EBO} | emitter-base voltage | open collector | – | 7 | V |
| I _C | collector current (DC) | | – | 1 | A |
| I _{CM} | peak collector current | | – | 1 | A |
| I _{BM} | peak base current | | – | 200 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | – | 800 | mW |
| | | T _{case} ≤ 25 °C | – | 5 | W |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | junction temperature | | – | 200 | °C |
| T _{amb} | operating ambient temperature | | –65 | +150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|-------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | in free air | 218 | K/W |
| R _{th j-c} | thermal resistance from junction to case | | 35 | K/W |

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CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-------------|--------------------------------------|---|----------|------|---------------|
| I_{CBO} | collector cut-off current | $I_E = 0; V_{CB} = 90\text{ V}$ | – | 10 | nA |
| | | $I_E = 0; V_{CB} = 90\text{ V}; T_{amb} = 150\text{ °C}$ | – | 10 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = 5\text{ V}$ | – | 10 | nA |
| h_{FE} | DC current gain | $V_{CE} = 10\text{ V}$; note 1 | | | |
| | | $I_C = 0.1\text{ mA}$ | 50 | – | |
| | | $I_C = 10\text{ mA}$ | 90 | – | |
| | | $I_C = 150\text{ mA}$ | 100 | 300 | |
| | | $I_C = 150\text{ mA}; T_{case} = -55\text{ °C}$ | 40 | – | |
| | | $I_C = 500\text{ mA}$ $I_C = 1\text{ A}$ | 50 15 | – | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 150\text{ mA}; I_B = 15\text{ mA}$ | – | 200 | mV |
| | | $I_C = 500\text{ mA}; I_B = 50\text{ mA}$; note 1 | – | 500 | mV |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 150\text{ mA}; I_B = 15\text{ mA}$; note 1 | – | 1.1 | V |
| C_c | collector capacitance | $I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$ | – | 12 | pF |
| C_e | emitter capacitance | $I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$ | – | 60 | pF |
| f_T | transition frequency | $I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 20\text{ MHz}$ | 100 | – | MHz |
| F | noise figure | $I_C = 0.1\text{ mA}; V_{CE} = 5\text{ V}; R_S = 1\text{ k}\Omega$; $f = 1\text{ kHz}; B = 200\text{ Hz}$ | – | 4 | dB |

Note1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.01$.

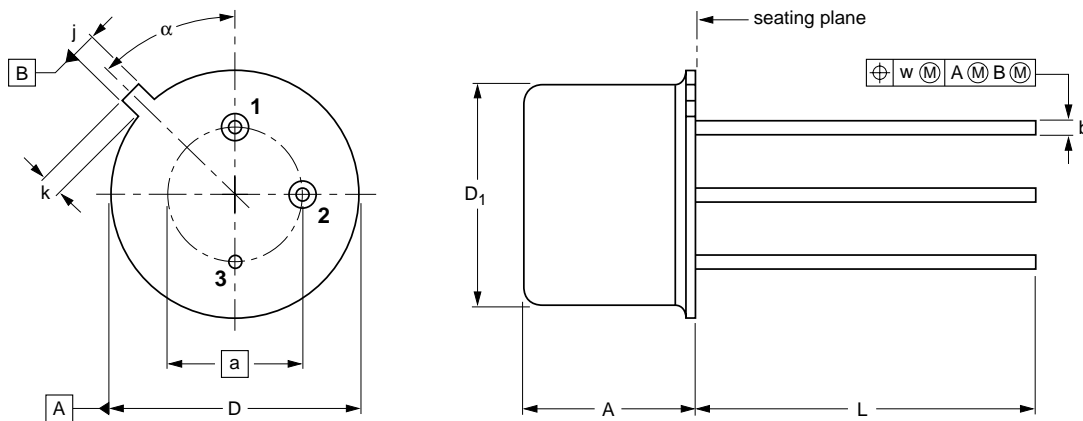
NPN medium power transistor

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PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

| UNIT | A | a | b | D | D ₁ | j | k | L | w | α |
|------|--------------|------|--------------|--------------|----------------|--------------|--------------|--------------|-----|-----|
| mm | 6.60 6.35 | 5.08 | 0.48 0.41 | 9.39 9.08 | 8.33 8.18 | 0.85 0.75 | 0.95 0.75 | 14.2 12.7 | 0.2 | 45° |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|--|---------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT5/11 | | TO-39 | | | | 97-04-11 |

NPN medium power transistor

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DEFINITIONS

| | |
|---|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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NPN medium power transistor

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